

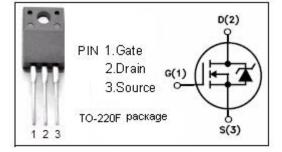
isc N-Channel MOSFET Transistor

2SK1710

DESCRIPTION

- Drain Current I_D= 6A@ T_C=25 °C
- · Drain Source Voltage
 - : V_{DSS}= 600V(Min)
- · Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



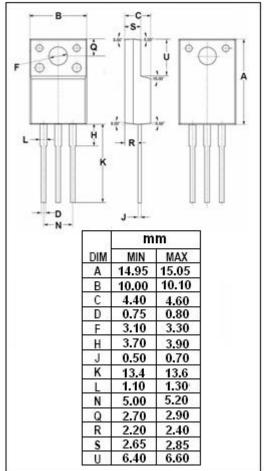


APPLICATIONS

· Power supplies, converters and power motor controls



SYMBOL	PARAMETER	VALUE	UNIT	
V _{DSS}	Drain-Source Voltage (V _{GS} =0)	600	V	
V_{GS}	Gate-Source Voltage	±30	٧	
I _D	Drain Current-continuous@ TC=25℃ 6		Α	
P _{tot}	Total Dissipation@TC=25℃	35	W	
Tj	Max. Operating Junction Temperature	150	$^{\circ}$ C	
T _{stg}	Storage Temperature Range	-55~150	$^{\circ}$ C	





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• ELECTRICAL CHARACTERISTICS (Tc=25°C)

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V _{GS} = 0; I _D = 1mA	600		V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =1mA	2.0	4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 3A		1.3	Ω
I _{GSS}	Gate-Body Leakage Current	V _{GS} = ±30V;V _{DS} = 0		±100	nA
IDSS	Zero Gate Voltage Drain Current	V _{DS} = 600V; V _{GS} = 0		1	mA



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